

L Number	Hits	Search Text	DB	Time stamp
279	0	5866263.URPN.	USPAT	2002/08/13 11:37
280	4	("4427992" "4900646" "5250845" "5401536").PN.	USPAT	2002/08/13 11:37
281	6	4427992.URPN.	USPAT	2002/08/13 11:39
282	6	4427992.URPN.	USPAT	2002/08/13 11:41
283	4	("2683667" "3528169" "3586926" "3789023").PN.	USPAT	2002/08/13 11:41
285	13	3586926.URPN.	USPAT	2002/08/13 11:42
294	1	5869560.URPN.	USPAT	2002/08/13 11:47
295	6	("5314941" "5416146" "5446064" "5478882" "5523355" "5554683").PN.	USPAT	2002/08/13 11:47
712	55	(adsorb\$3 adsorption) with (((("si" silicon) with (fluorine))or si\$2f)	EPO; JPO; DERWENT	2002/08/13 15:55
720	10	(adsorb\$3 adsorption) with (((("si" silicon) with (fluorine))or si\$2f) with (organic or carbon)	USPAT; US-PGPUB; IBM_TDB	2002/08/13 15:55
724	8	(adsorb\$3 adsorption) with (((("si" silicon) with (fluorine))or si\$2f) with (organic or carbon)	EPO; JPO; DERWENT	2002/08/13 12:45
716	102	(adsorb\$3 adsorption) with (((("si" silicon) with (fluorine))or si\$2f)	USPAT; US-PGPUB; IBM_TDB	2002/08/13 14:19
728	0	(adsorb\$3 adsorption) with (si\$1f) with bond	EPO; JPO; DERWENT	2002/08/13 14:24
732	0	(adsorb\$3 adsorption) with "si-f" with bond	EPO; JPO; DERWENT	2002/08/13 14:24
736	0	(adsorb\$3 adsorption) with "sif" with bond	EPO; JPO; DERWENT	2002/08/13 14:24
740	0	(adsorb\$3 adsorption) with "si--f" with bond	EPO; JPO; DERWENT	2002/08/13 14:24
744	4	(adsorb\$3 adsorption) with "si--f" with bond	USPAT; US-PGPUB; IBM_TDB	2002/08/13 14:26
748	100	(adsorb\$3 adsorption) with silicon with fluori\$3	USPAT; US-PGPUB; IBM_TDB	2002/08/13 14:26
752	0	(adsorb\$3 adsorption) with silicon with fluori\$3 with (organic with carbon)	USPAT; US-PGPUB; IBM_TDB	2002/08/13 14:27
760	9	(adsorb\$3 adsorption) with silicon with fluori\$3 with (organic carbon)	USPAT; US-PGPUB; IBM_TDB	2002/08/13 14:27
756	10	((adsorb\$3 adsorption) with silicon with fluori\$3) same (organic carbon)	USPAT; US-PGPUB; IBM_TDB	2002/08/13 14:27
769	1		USPAT; US-PGPUB; JPO; DERWENT	2002/08/13 14:37
774	37	method same ("gate oxide" with polysilicon with hole)	USPAT; US-PGPUB; JPO; DERWENT	2002/08/13 15:41
784	0	("gate oxide" with polysilicon with hole) and ((stor\$3 transfer\$3) with (adsorb\$4 adsorp\$4))	IBM_TDB	2002/08/13 14:42
779	1	("gate oxide" with polysilicon with hole) and ((stor\$3 transfer\$3) with (adsorb\$4 adsorp\$4))	USPAT; US-PGPUB; JPO; DERWENT	2002/08/13 14:43
785	2	("gate oxide" with polysilicon with hole) and (adsorb\$4 adsorp\$4)	USPAT; US-PGPUB; JPO; DERWENT	2002/08/13 14:45
790	0	("gate oxide" with polysilicon with hole) and (adsorb\$4 adsorp\$4)	IBM_TDB	2002/08/13 14:44

791	9	(gate with polysilicon with hole) and (adsorb\$4 adsorp\$4)	USPAT; US-PGPUB; JPO;	2002/08/13 14:48
796	0	(gate with polysilicon with hole) and (adsorb\$4 adsorp\$4)	DERWENT IBM_TDB	2002/08/13 14:48
797	699	adsorbent with between with process\$3	USPAT; US-PGPUB; JPO;	2002/08/13 15:01
802	25	adsorbent with between with process\$3 with (film deposit\$3 layer)	DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 15:03
807	31	adsorbent with between with process\$3 with (semiconductor wafer substrate film deposit\$3 layer)	DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 15:07
812	313	(adsorbent adsorb adsorption) with between with (process\$3 step method) with (semiconductor wafer substrate film deposit\$3 layer)	DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 15:15
817	51	(adsorbent adsorb adsorption) with between with (process\$3 step method) with (semiconductor wafer substrate film deposit\$3 layer) with (carbon organic)	DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 15:17
822	0	118/719.ccls. and ("gate oxide" with polysilicon with hole)	DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 15:42
827	0	(multi\$4 with chamber) and ("gate oxide" with polysilicon with hole)	DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 15:43
828	0	((multi multiple) with chamber) and ("gate oxide" with polysilicon with hole)	DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 15:44
833	0	((transfer) with chamber) and ("gate oxide" with polysilicon with hole)	DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 15:44
838	1	((transfer\$3 stor\$3) with chamber) and ("gate oxide" with polysilicon with hole)	DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 15:45
843	19	(absorb) with (((("si" silicon) with (fluorine))or si\$2f)	DERWENT EPO; JPO;	2002/08/13 15:56
851	65	(absorb\$3) with (((("si" silicon) with (fluorine))or si\$2f)	DERWENT EPO; JPO;	2002/08/13 16:06
847	14	(absorb\$3) with (((("si" silicon) with (fluorine))or si\$2f) with (organic or carbon)	DERWENT USPAT; US-PGPUB;	2002/08/13 15:57
855	1	"11259078"	IBM_TDB	2002/08/13 18:16
-	38983	c23c016\$.ipc.	JPO;	2002/08/12 12:36
-	660865	h011021\$.ipc.	DERWENT JPO;	2002/08/12 12:36
-	117	(156/345.31).CCLS.	DERWENT USPAT;	2002/08/12 12:16
-	0	(156/345.31 and (adsorb adsorption absorb)).CCLS.	US-PGPUB USPAT;	2002/08/12 12:17
-	23	156/345.31.ccls. and (adsorb adsorption absorb)	US-PGPUB USPAT;	2002/08/12 12:26

-	169	(118/715-733.ccls. 156/345.1-345.55.ccls.) and ((adsorb\$2 adsorption absorb) with (cassette vessel apparatus store storage transfer stock))	USPAT; US-PGPUB	2002/08/12 12:30
-	0	"08346836"		
-	0	"08-346836"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/08/12 12:30
-	0	"080346836"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/08/12 12:29
-	0	10-181881	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/08/12 12:29
-	2	container with seal with adsorbing	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/08/12 12:30
-	1	semiconductor with adsorbing with contaminants	EPO; JPO; DERWENT	2002/08/12 12:32
-	1	clarification with degree with sealing	EPO; JPO; DERWENT	2002/08/12 12:34
-	40400	c23c016\$.ipc.	EPO; JPO; DERWENT	2002/08/12 12:35
-	677136	h011021\$.ipc.	JPO; DERWENT	2002/08/12 12:36
-	1320	(c23c016\$.ipc. h011021\$.ipc.) and ((adsorb\$3 adsorption absorb) with (cassette vessel apparatus store storage transfer stock container))	JPO; DERWENT	2002/08/12 12:36
-	187	(118/715-733.ccls. 156/345.1-345.55.ccls.) and ((adsorb\$3 adsorption absorb) with (cassette vessel apparatus store storage transfer stock container))	EPO; JPO; DERWENT	2002/08/12 12:38
-	760	(c23c016\$.ipc. h011021\$.ipc.) and (((adsorb\$3 adsorption absorb) with (cassette vessel apparatus store storage transfer stock container)) same (semiconductor wafer substrate))	USPAT; US-PGPUB	2002/08/12 15:01
-	391	(c23c016\$.ipc. h011021\$.ipc.) and (((adsorb\$3 adsorption absorb) with (cassette vessel apparatus store storage transfer stock container)) same (stor\$3 transfer\$3))	EPO; JPO; DERWENT	2002/08/12 12:39
-	8	(c23c016\$.ipc. h011021\$.ipc.) and (((adsorb\$3 adsorption absorb) with (cassette vessel apparatus store storage transfer stock container)) same (stor\$3 transfer\$3) same organic)	EPO; JPO; DERWENT	2002/08/12 13:48
-	1	("5863808").PN.	EPO; JPO; DERWENT	2002/08/12 12:49
-	2	("5105628" "5551984").PN.	USPAT; US-PGPUB	2002/08/12 12:50
-	0	5863808.URPN.	USPAT	2002/08/12 13:01
-	26	"0259078"	USPAT	2002/08/12 13:02
-	27	"0259078"	EPO; JPO; DERWENT	2002/08/12 13:57
-	4958	(adsorb\$3 adsorption) with (cassette vessel apparatus store storage transfer stock container) with (stor\$3 transfer\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/08/12 13:57
-	2582	(adsorb\$3 adsorption) with (cassette vessel apparatus storage stock container) with (stor\$3 transfer\$3)	USPAT; US-PGPUB	2002/08/12 15:00
-	8	(118/715-733.ccls. 156/345.1-345.55.ccls.) and ((adsorb\$3 adsorption) with (cassette vessel apparatus storage stock container) with (stor\$3 transfer\$3))	USPAT; US-PGPUB	2002/08/12 15:01
-	1	("4851018").PN.	USPAT; US-PGPUB	2002/08/12 15:37
-			USPAT; US-PGPUB	2002/08/12 15:03

-	29	4851018.URPN.	USPAT	2002/08/12 15:03
-	590	((adsorb\$3 adsorption) with (cassette vessel apparatus storage stock container) with (stor\$3 transfer\$3)) same (carbon organic)	USPAT; US-PGPUB	2002/08/12 15:39
-	104	((adsorb\$3 adsorption) with (cassette vessel apparatus storage stock container) with (stor\$3 transfer\$3)) same (semiconductor wafer substrate)	USPAT; US-PGPUB	2002/08/12 16:08
-	7	5498118.URPN.	USPAT	2002/08/12 15:45
-	4	6048655.URPN.	USPAT	2002/08/12 15:46
-	11	("4539695" "4758127" "4770590" "4984953" "5026239" "5102280" "5183370" "5301013" "5308222" "5405230" "5498118").PN.	USPAT	2002/08/12 15:47
-	6	("4178113" "4493606" "4550242" "4759681" "4938655" "4988252").PN.	USPAT	2002/08/12 15:48
-	27	5183370.URPN.	USPAT	2002/08/12 15:49
-	0	20010027028.URPN.	USPAT	2002/08/12 16:01
-	8	("4471716" "4724874" "4963069" "5207548" "5255797" "5346518" "5749469" "5843196").PN.	USPAT	2002/08/12 16:07
-	1	((adsorb\$3 adsorption) and ("4471716" "4724874" "4963069" "5207548" "5255797" "5346518" "5749469" "5843196").PN.))	USPAT; US-PGPUB	2002/08/12 16:13
-	16	5346518.URPN.	USPAT	2002/08/12 16:12
-	8	((adsorb\$3 adsorption) and 5346518.URPN.)	USPAT; US-PGPUB	2002/08/12 16:15
-	1067	(adsorb\$3 adsorption) same(("si" silicon) with (wafer substrate))	USPAT; US-PGPUB	2002/08/12 16:17
-	17	(adsorb\$3 adsorption) same(("si" silicon) with (wafer substrate) with (coat\$3 deposit\$3 film) with (fluorine si\$1f))	USPAT; US-PGPUB	2002/08/12 16:29
-	319	(adsorb\$3 adsorption) with ("si" silicon) with (wafer substrate) with (coat\$3 deposit\$3 film treat\$3)	USPAT; US-PGPUB	2002/08/12 16:36
-	0	118/&.ccls. and((adsorb\$3 adsorption) with ("si" silicon) with (wafer substrate) with (coat\$3 deposit\$3 film treat\$3))	USPAT; US-PGPUB	2002/08/12 16:36
-	210	((adsorb\$3 adsorption) with ("si" silicon) with (wafer substrate) with (coat\$3 deposit\$3 film treat\$3))	EPO; JPO; DERWENT	2002/08/12 16:39
-	9	118/\$.ccls. and((adsorb\$3 adsorption) with ("si" silicon) with (wafer substrate) with (coat\$3 deposit\$3 film treat\$3))	USPAT; US-PGPUB	2002/08/12 16:37
-	119	(c23c016\$.ipc. h011021\$.ipc.) and ((adsorb\$3 adsorption) with ("si" silicon) with (wafer substrate) with (coat\$3 deposit\$3 film treat\$3))	EPO; JPO; DERWENT	2002/08/13 09:49
-	10	(c23c016\$.ipc. h011021\$.ipc.) and ((adsorb\$3 adsorption) with ("sif" "si-f" ((silicon "si") with ("f" fluorine))) with (wafer substrate) with (coat\$3 deposit\$3 film treat\$3))	EPO; JPO; DERWENT	2002/08/13 09:18
-	6	((adsorb\$3 adsorption) with ("si" silicon) with (wafer substrate) with (transfer\$3 stor\$3))	EPO; JPO; DERWENT	2002/08/13 09:50
-	13	((adsorb\$3 adsorption) with ("si" silicon) with (wafer substrate) with (transfer\$3 stor\$3))	USPAT; US-PGPUB	2002/08/13 10:05
-	47	((adsorb\$3 adsorption) with ("si" silicon) with (transfer\$3 stor\$3))	USPAT; US-PGPUB	2002/08/13 10:13
-	25	((adsorb\$3 adsorption) with ("si" silicon) with (transfer\$3 stor\$3))	EPO; JPO; DERWENT	2002/08/13 12:29
-	610	((adsorb\$3 adsorption) with ("si" silicon) with (wafer substrate semiconductor))	USPAT; US-PGPUB	2002/08/13 10:19